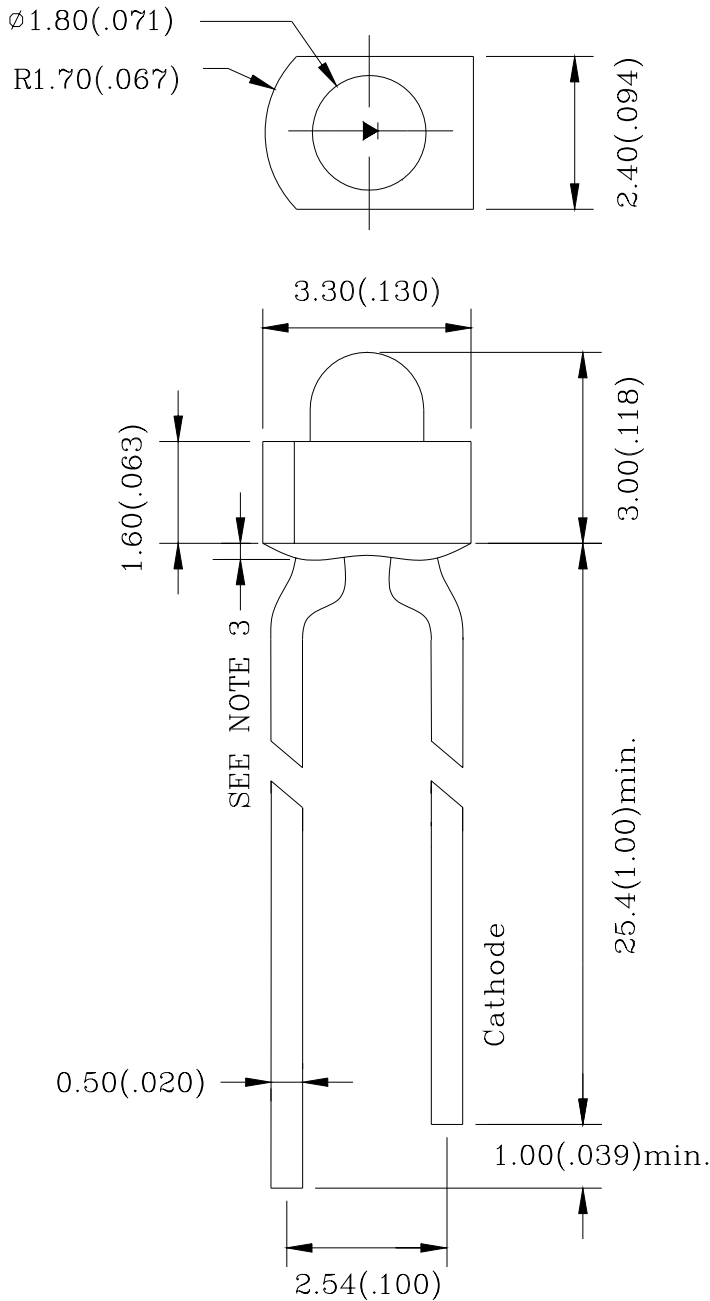


**PACKAGE DIMENSIONS**



- Note:**
- 1.All Dimensions are in millimeters.
  - 2.Tolerance is  $\pm 0.25\text{mm}(0.010 \text{ "})$  Unless otherwise specified.
  - 3.Protruded resin under flange is  $1.5\text{mm}(0.059 \text{ "})$  max.
  - 4.Lead spacing is measured where the leads emerge from the package.
  - 5.Specification are subject to change without notice.

**FEATURES**

- \* 1.8 mm DIA TOWER TYPE LED LAMP
- \* HIGH LUMINOUS INTENSITY OUTPUT.
- \* LOW POWER CONSUMPTION.
- \* HIGH EFFICIENCY.
- \* VERSATILE MOUNTING ON P.C. BOARD OR PANEL.
- \* I.C. COMPATIBLE.

**CHIP MATERIALS**

- \* Dice Material : GaAlInP/GaAs
- \* Light Color : ULTRA RED
- \* Lens Color : RED DIFFUSED

**ABSOLUTE MAXIMUM RATING : ( Ta = 25°C )**

SYMBOL	PARAMETER	ULTRA RED	UNIT
PAD	Power Dissipation Per Chip	80	mW
VR	Reverse Voltage Per Chip	5	V
IAF	Continuous Forward Current Per Chip	30	mA
IPF	Peak Forward Current Per Chip (Duty – 0.1, 1KHz)	60	mA
—	Derating Linear From 25°C Per Chip	0.40	mA/°C
Topr	Operating Temperature Range	-25°C to 85°C	
Tstg	Storage Temperature Range	-40°C to 85°C	
Lead Soldering Temperature { 1.6mm(0.063 inch) From Body } 260°C ± 5°C for 5 Seconds			

**ELECTRO-OPTICAL CHARACTERISTICS : ( Ta = 25°C )**

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
VF	Forward Voltage	IF = 20mA		2.0		V
IR	Reverse Current	VR = 5V			100	µA
λD	Dominant Wavelength	IF = 20mA		630		nm
Δλ	Spectral Line Half-Width	IF = 20mA		20		nm
2θ1/2	Half Intensity Angle	IF = 20mA		50		deg
IV	Luminous Intensity	IF = 20mA		900		mcd

